



## 2.5A MOSFET/IGBT Gate Driver Optocoupler

### Features

- Peak Output Current : IOP =  $\pm 2.5A$  (max)
- Threshold Input Current: IFLH = 5 mA (max)
- Common mode transient immunity :  $\pm 20kV/\mu s$  (min)
- Under voltage lock out (UVLO) protection with hysteresis
- Pb free and RoHS compliant.

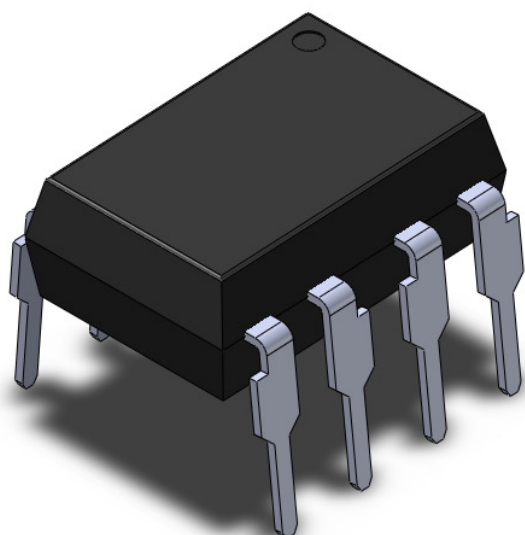
### Applications

- Isolated IGBT/Power MOSFET gate drive
- Industrial Inverter
- AC brushless and DC motor drives
- Induction Heating

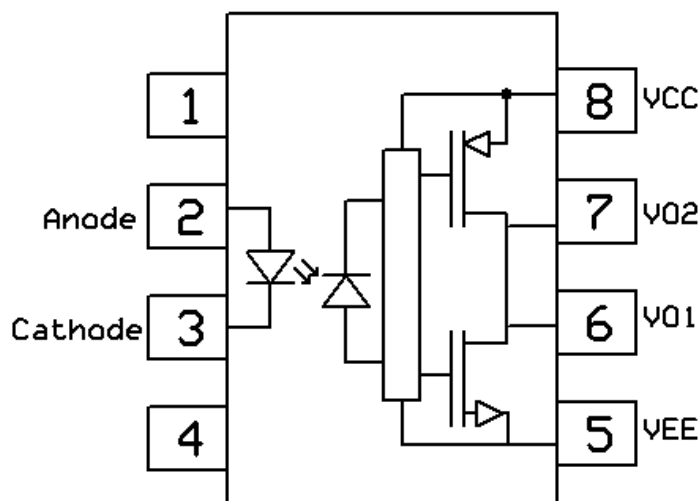
### Description

The CT350 consists of a GaAsP LED optically coupled to an integrated circuit with a power output stage. This optocoupler is ideally suited for driving power IGBTs and MOSFETs used in motor control inverter applications. The high operating voltage range of the output stage provides the drive voltages required by gate controlled devices.

### Package Outline



### Schematic



Note: Different lead forming options available. See package dimension.



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## Truth Table

LED	V <sub>CC</sub> -V <sub>EE</sub> Positive Going	V <sub>CC</sub> -V <sub>EE</sub> Negative Going	Output
Off	0 to 30 V	0 to 30V	Low
On	0 to 11.5V	0 to 10V	Low
On	11.5 to 13.5V	10 to 12V	Transition
On	13.5 to 30V	12 to 30V	High

## Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
V <sub>ISO</sub>	Isolation voltage	3750	V <sub>RMS</sub>	1
T <sub>OPR</sub>	Operating temperature	-40 ~ +100	°C	
T <sub>STG</sub>	Storage temperature	-55 ~ +125	°C	
T <sub>SOL</sub>	Soldering temperature	260	°C	2
P <sub>T</sub>	Total Power Dissipation	300	mW	
f <sub>OPR</sub>	Operating Frequency	50	kHz	3
<b>Emitter</b>				
I <sub>F</sub>	Forward current	25	mA	
I <sub>FP</sub>	Peak forward current (50% duty, 1ms P.W)	1	A	
V <sub>R</sub>	Reverse voltage	5	V	
<b>Detector</b>				
P <sub>D</sub>	Power dissipation	250	mW	
V <sub>O(PEAK)</sub>	Peak Output Voltage	35	V	
I <sub>OPH</sub>	Output High Peak Current	-2.5	A	4
I <sub>OPL</sub>	Output Low Peak Current	2.5	A	4
V <sub>CC</sub>	Supply voltage	0 to 35	V	

## Notes

1. AC for 1 minute, RH = 40 ~ 60%.
2. For 10 second peak
3. Exponential Waveform, I<sub>O(PEAK)</sub> ≤ |2.5A|, Pulse Width ≤ 0.3us
4. Pulse Width = 10uS, DC = 1.0%



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### Electrical Characteristics

Typical values are measured at  $T_A = -40^{\circ}\text{C}$  to  $100^{\circ}\text{C}$  (unless otherwise stated)

#### Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_F$	Forward voltage	$I_F = 10\text{mA}$	--	1.45	1.8	V	
$V_R$	Reverse Voltage	$I_R = 10\mu\text{A}$	5.0	-	-	V	
$\Delta V_F/\Delta T_A$	Temperature coefficient of forward voltage	$I_F = 10\text{mA}$	--	-1.8	--	mV/ $^{\circ}\text{C}$	

#### Detector Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$I_{CCL}$	Logic Low Supply Current	$I_F = 0\text{mA}$ , $V_O = \text{Open}$	--	1.5	2.0	mA	
$I_{CCH}$	Logic High Supply Current	$I_F = 10\text{mA}$ , $V_O = \text{Open}$	--	1.7	2.2	mA	

#### Transfer Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes
$V_{OH}$	High Level Output Voltage	$I_F = 5\text{mA}$ , $V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ , $R_L = 200\ \Omega$	11.0	13.7	--	V	
$V_{OL}$	Low Level Output Voltage	$V_F = 0.8\text{V}$ , $V_{CC1} = +15\text{V}$ , $V_{EE1} = -15\text{V}$ , $R_L = 200\ \Omega$	--	-14.9	-12.5	V	
$I_{OPH}$	High Level Output Current	$I_F = 5\text{mA}$ , $V_{CC} = 30\text{V}$ $V_{8-6} = -3.5\text{V}$	--	-1.6	-1.0	A	
		$I_F = 5\text{mA}$ , $V_{CC} = 15\text{V}$ $V_{8-6} = -7.0\text{V}$	--	--	-2.0		
$I_{OPL}$	Low Level Output Current	$I_F = 0\text{mA}$ , $V_{CC} = 30\text{V}$ $V_{6-5} = 2.5\text{V}$	1.0	1.6	--	A	
		$I_F = 0\text{mA}$ , $V_{CC} = 15\text{V}$ $V_{6-5} = 7\text{V}$	2.0	--	--		
$I_{FHL}$	Input Threshold Current	$V_{CC} = 15\text{V}$ , $I_O = 0\text{mA}$ , $V_O > 1\text{V}$	--	1.8	5.0	mA	
$V_{FHL}$	Input Threshold Voltage	$V_{CC} = 15\text{V}$ , $I_O = 0\text{mA}$ , $V_O < 1\text{V}$	0.8	--	--	V	
$V_{UVLO+}$	Under Voltage Lockout Threshold	$I_F = 5\text{mA}$ , $V_O > 2.5\text{V}$	11.0	12.5	13.5	V	
$V_{UVLO-}$		$I_F = 5\text{mA}$ , $V_O < 2.5\text{V}$	9.5	11.0	12.2		



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## Switching Characteristics

Symbol	Parameters	Test Conditions	Min	Typ	Max	Units	Notes	
$T_{PHL}$	High to Low Propagation Delay	$I_F = 5\text{mA}$ , $C_g = 10\text{nF}$ , $R_L = 20\Omega$ , $f = 10\text{kHz}$ , Duty = 50%, $T_A = 25\text{ }^\circ\text{C}$	50	170	500	ns		
$T_{PLH}$	Low to High Propagation Delay		50	180	500	ns		
$P_{WD}$	Pulse Width Distortion		--	10	100	ns		
$t_{PSK}$	Propagation Delay Skew		--	--	40	ns		
$t_r$	Rise Time		--	15	--	ns		
$t_f$	Fall Time		--	8	--	ns		
$t_{UVLO(ON)}$	UVLO Turn On Delay	$I_F = 5\text{mA}$ , $V_O > 5\text{V}$	--	2.5	--	$\mu\text{s}$		
$t_{UVLO(OFF)}$	UVLO Turn Off Delay	$I_F = 5\text{mA}$ , $V_O < 5\text{V}$	--	0.4	--	$\mu\text{s}$		
$ CM_H $	Common Mode Transient High	$V_{CC} = 30\text{V}$ , $R_L = 350\Omega$ , $T_A = 25\text{ }^\circ\text{C}$ , $V_{CM} = 1\text{kV}$	$I_F = 5\text{mA}$	-15	--	--	$\text{kV}/\mu\text{s}$	
$ CM_L $	Common Mode Transient Low		$I_F = 0\text{mA}$	15	--	--	$\text{kV}/\mu\text{s}$	



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## Typical Characteristic Curves

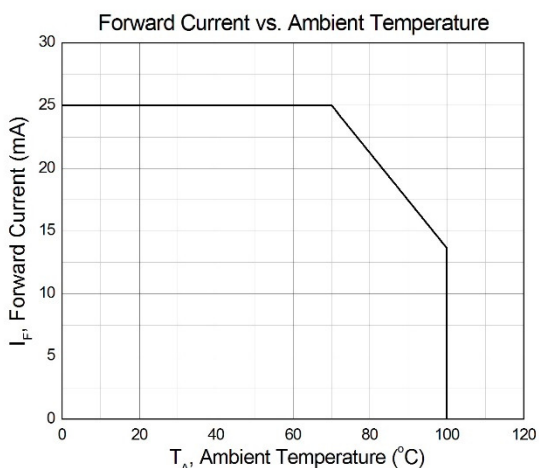


Figure 1

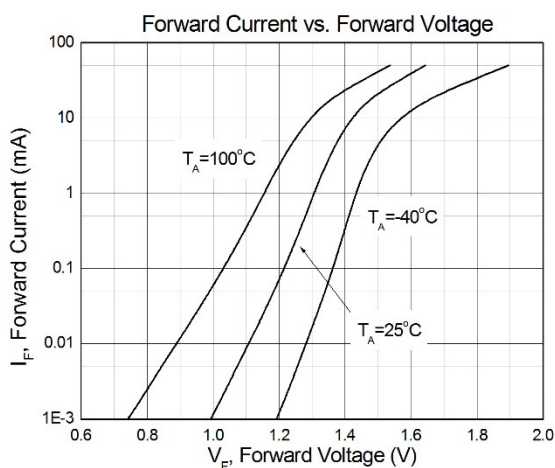


Figure 2

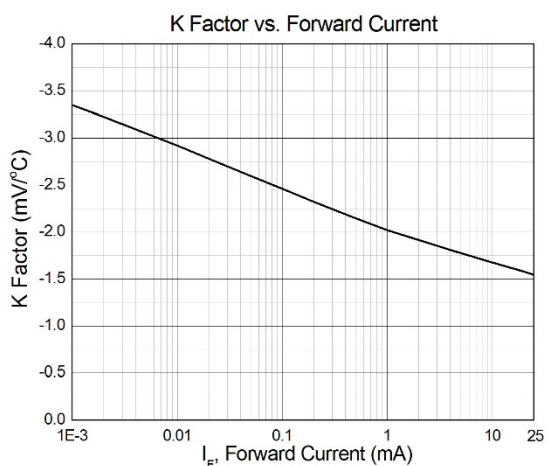


Figure 3

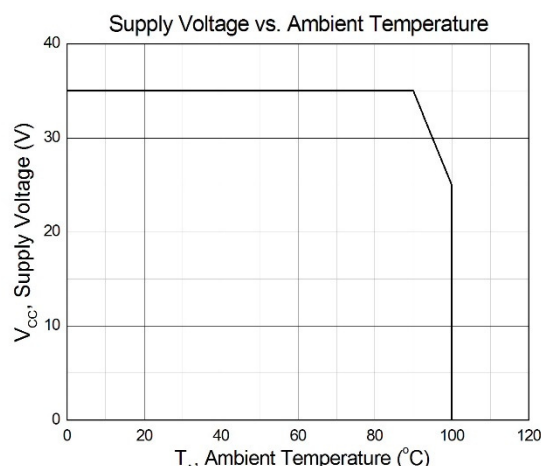


Figure 4

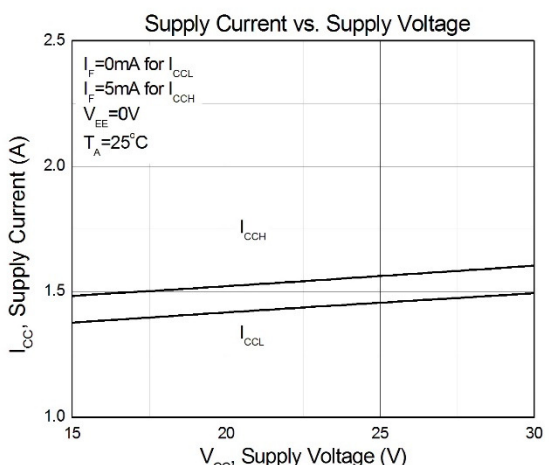


Figure 5

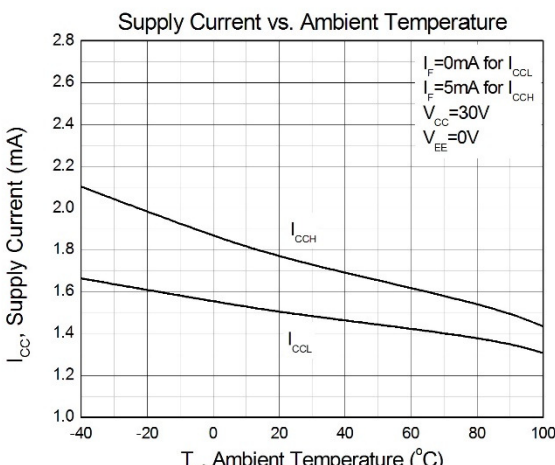


Figure 6



# 2.5A MOSFET/IGBT Gate Driver Optocoupler

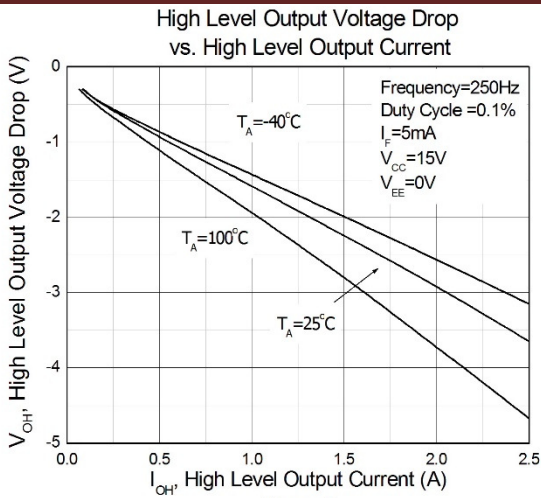


Figure 7

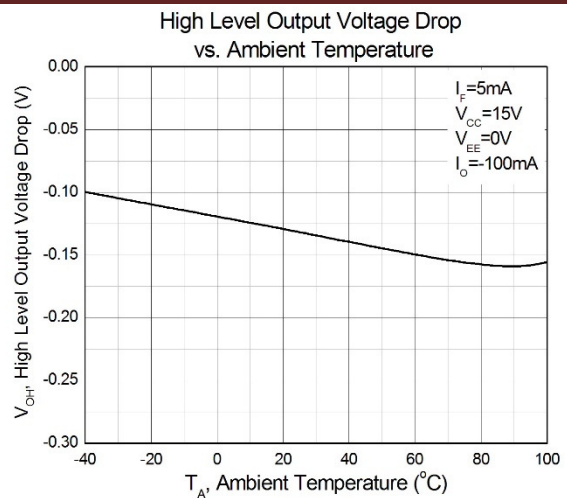


Figure 8

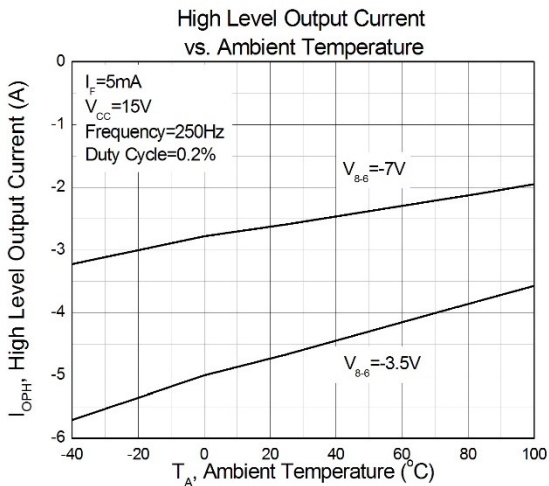


Figure 9

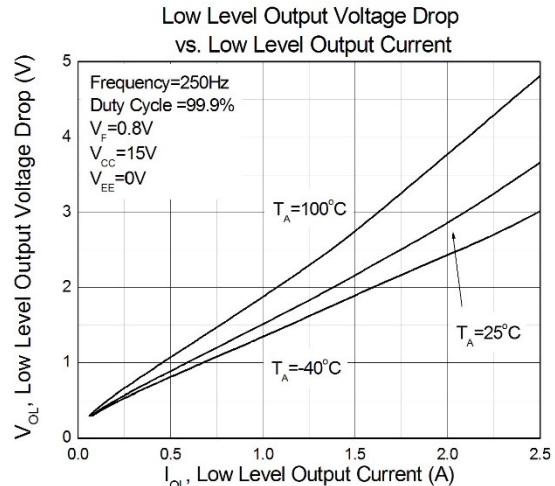


Figure 10

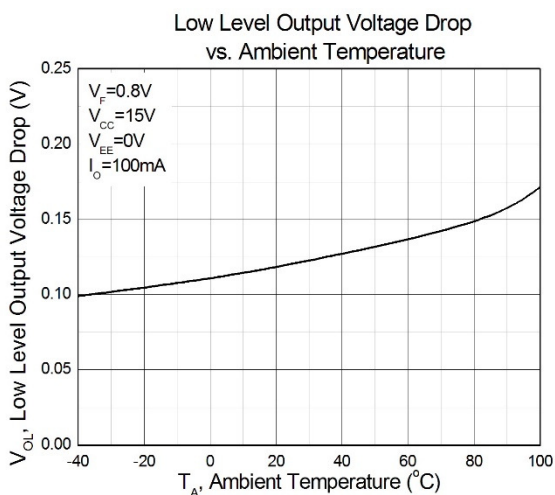


Figure 11

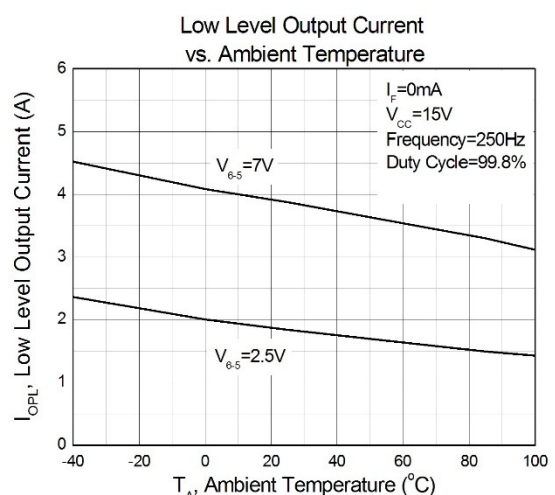
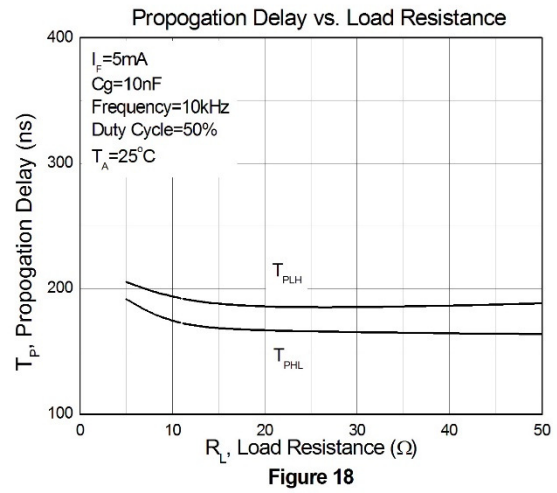
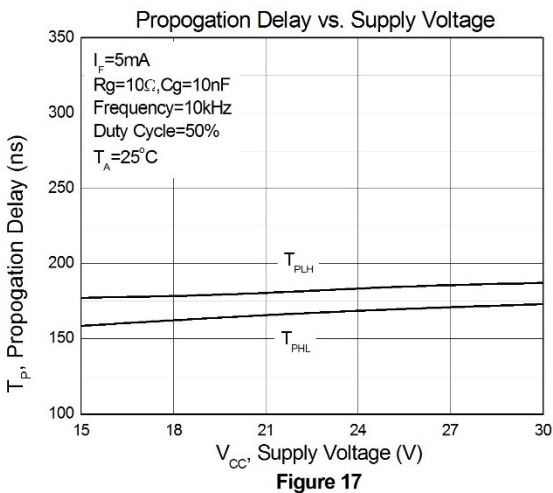
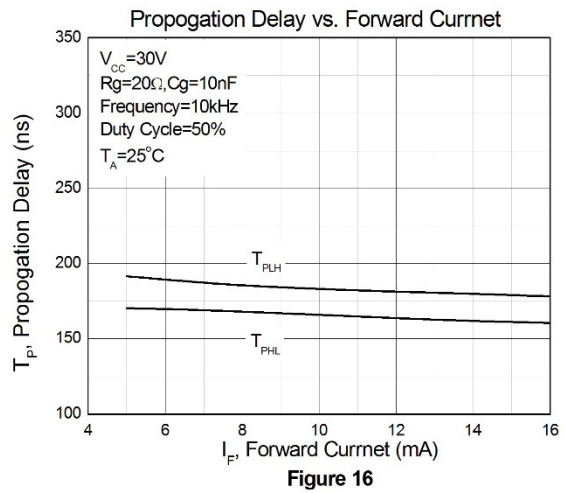
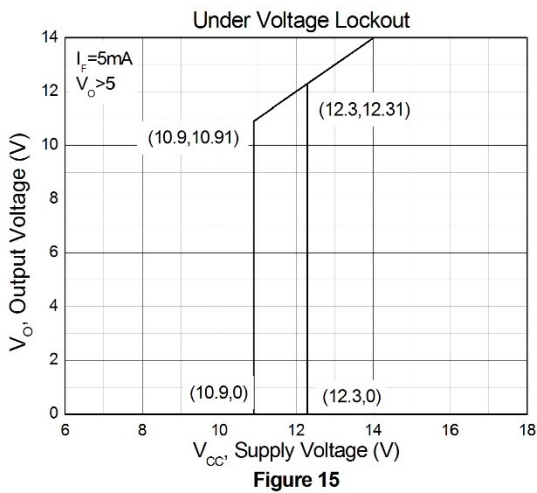
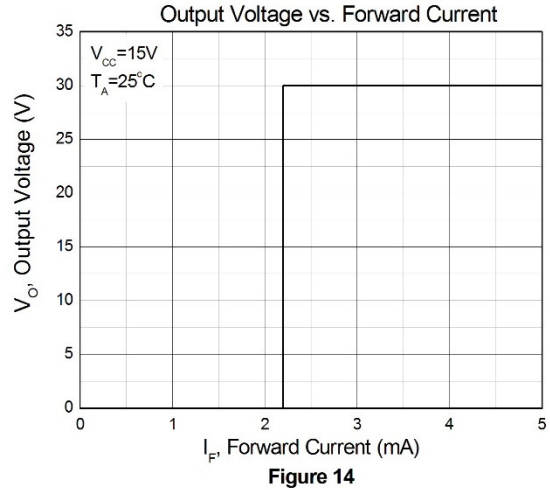
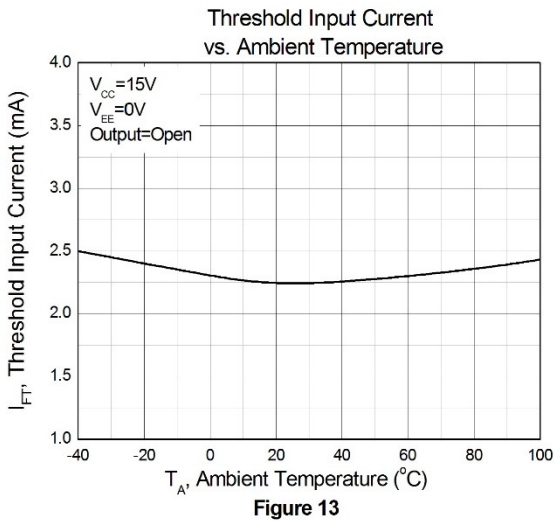


Figure 12



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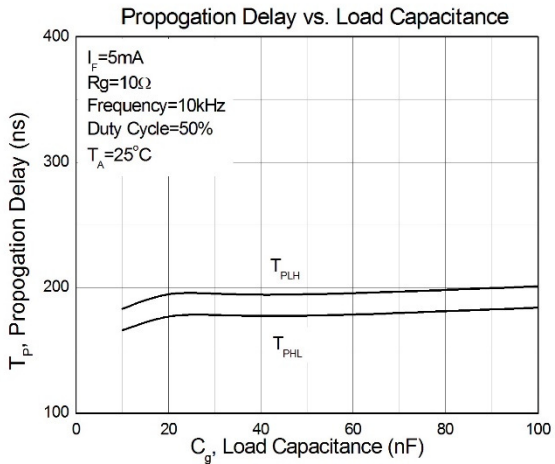


Figure 19

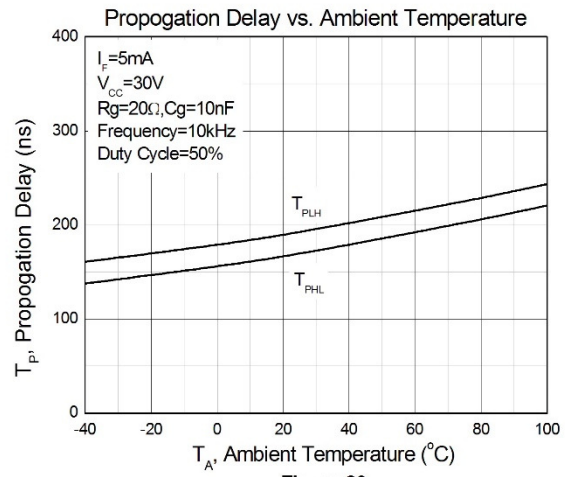


Figure 20

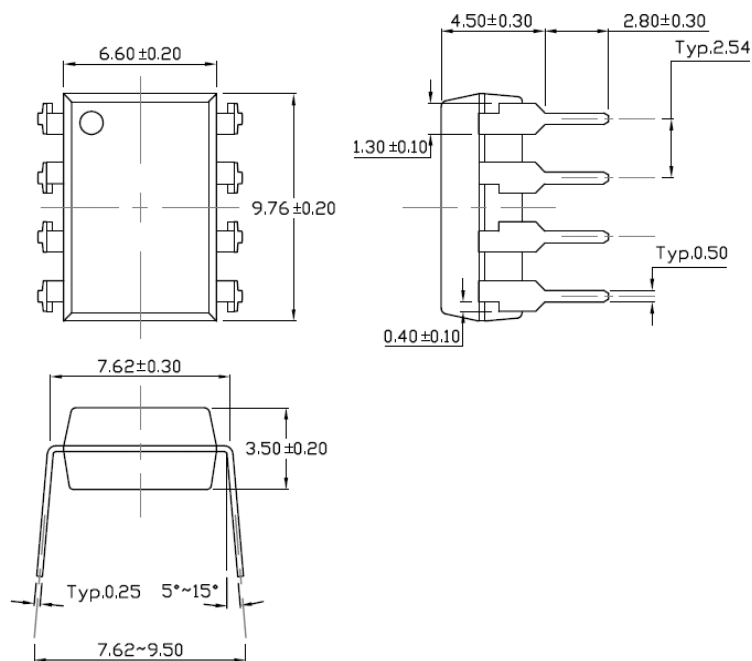




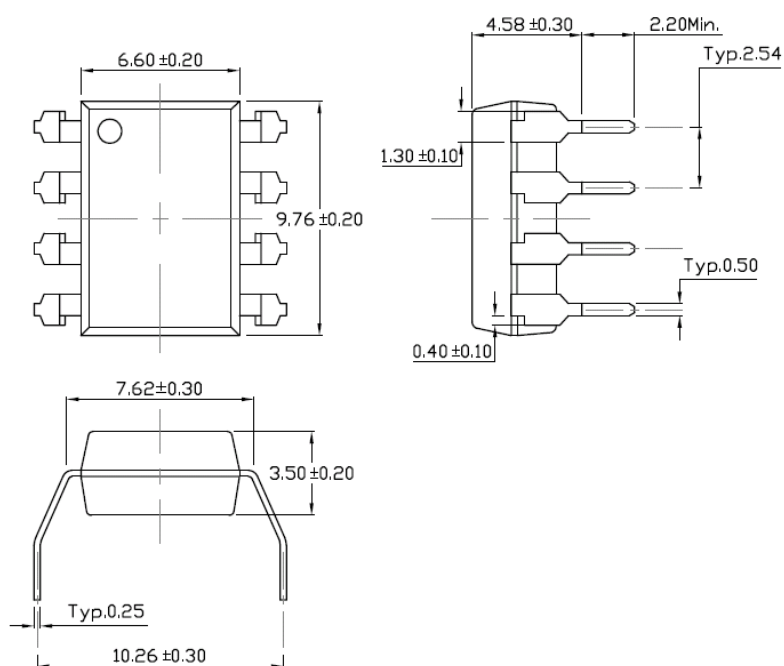
# 2.5A MOSFET/IGBT Gate Driver Optocoupler

## Package Dimension *Dimensions in mm unless otherwise stated*

### Standard DIP – Through Hole



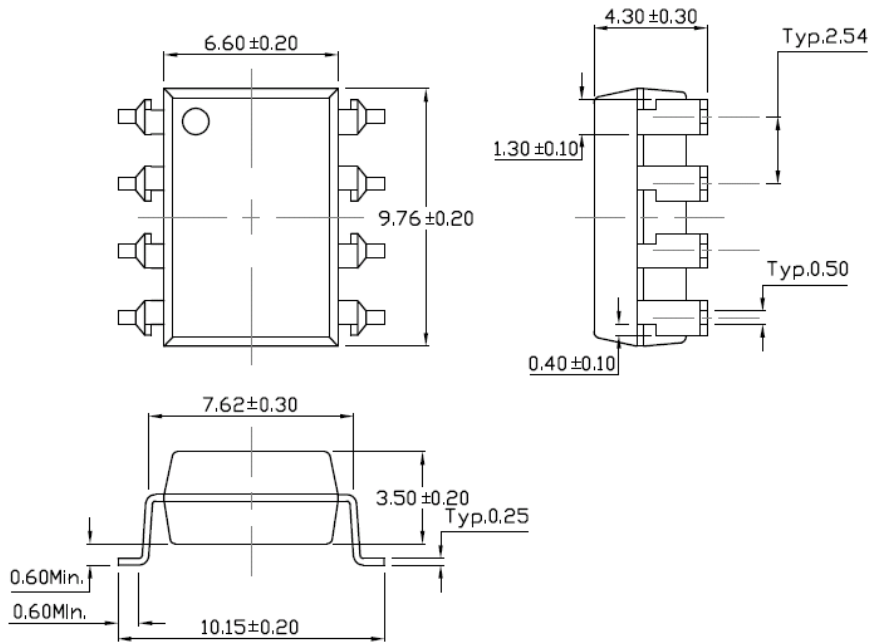
### Gullwing (400mil) Lead Forming – Through Hole



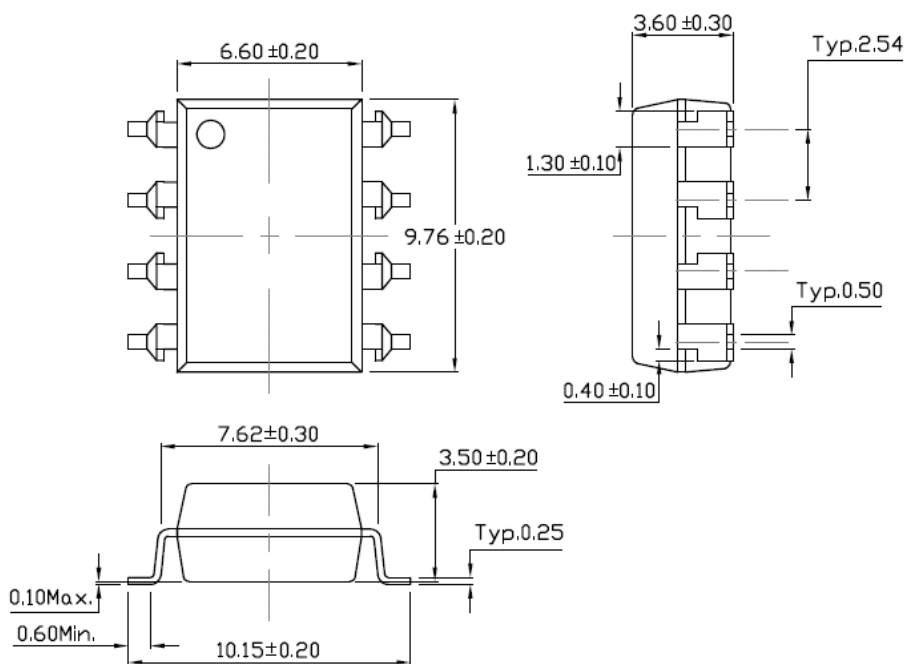


## 2.5A MOSFET/IGBT Gate Driver Optocoupler

### Surface Mount Lead Forming



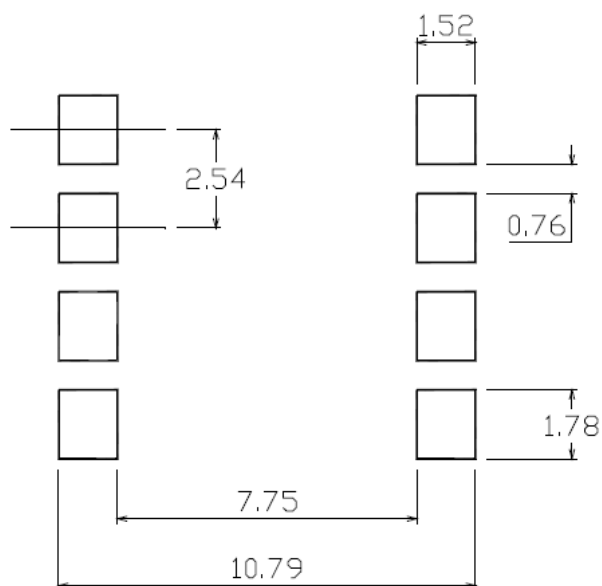
### Surface Mount (Low Profile) Lead Forming



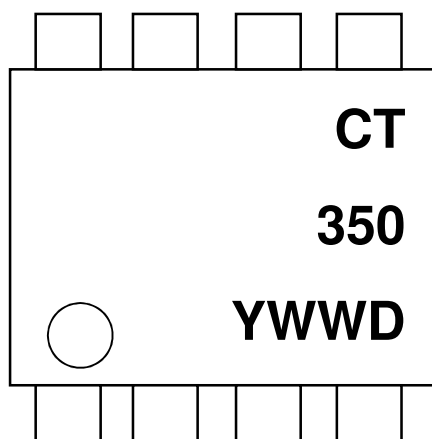


## 2.5A MOSFET/IGBT Gate Driver Optocoupler

### Recommended Solder Mask Dimensions in mm unless otherwise stated



### Device Marking



#### Note:

- CT : Denotes "CT Micro"
- 350 : Product Number
- Y : Fiscal Year
- WW : Work Week
- D : Production Code



## 2.5A MOSFET/IGBT Gate Driver Optocoupler

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### Ordering Information

#### CT350(Y)(Z)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1, T2 or none)

<i>Option</i>	<i>Description</i>	<i>Quantity</i>
None	Standard 8 Pin Dip	45 Units/Tube
M	Gullwing (400mil) Lead Forming	45 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1000 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	1000 Units/Reel

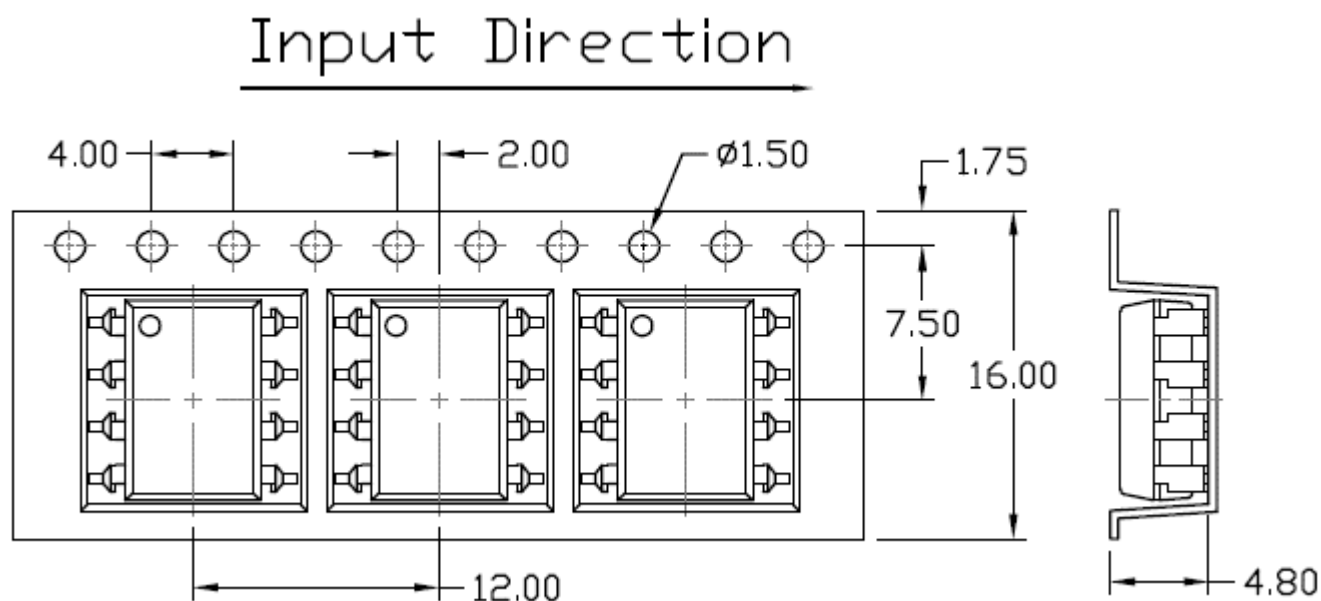


CT350

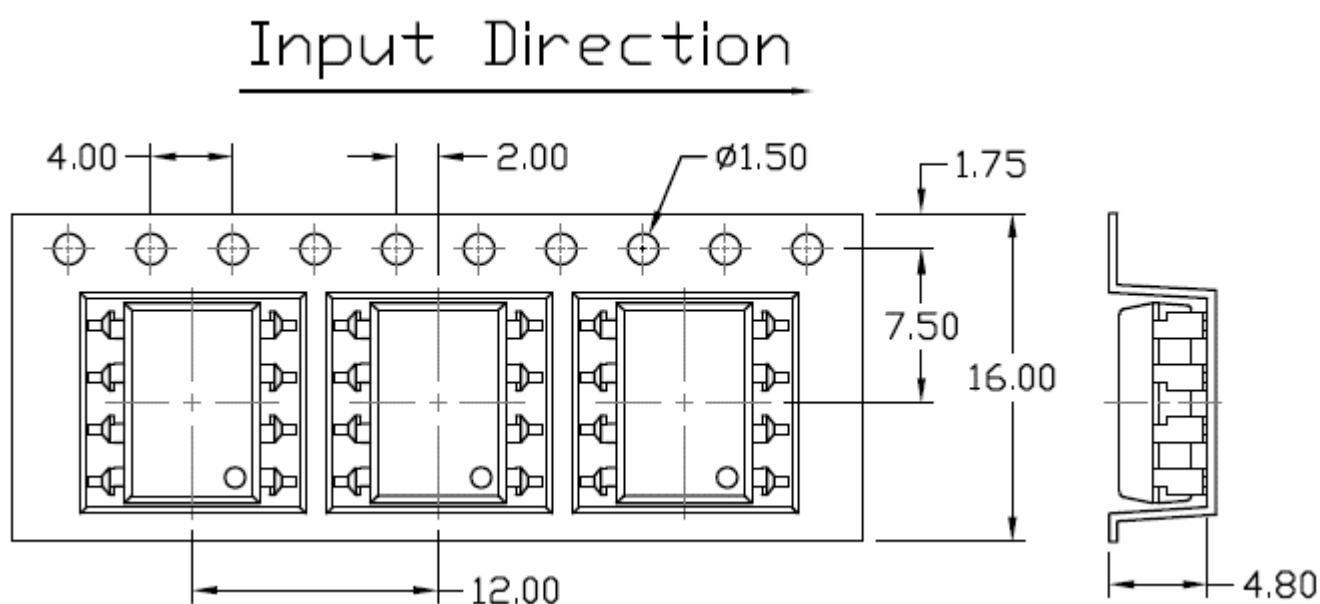
## 2.5A MOSFET/IGBT Gate Driver Optocoupler

### Carrier Tape Specifications *Dimensions in mm unless otherwise stated*

#### Option S(T1) & SL(T1)



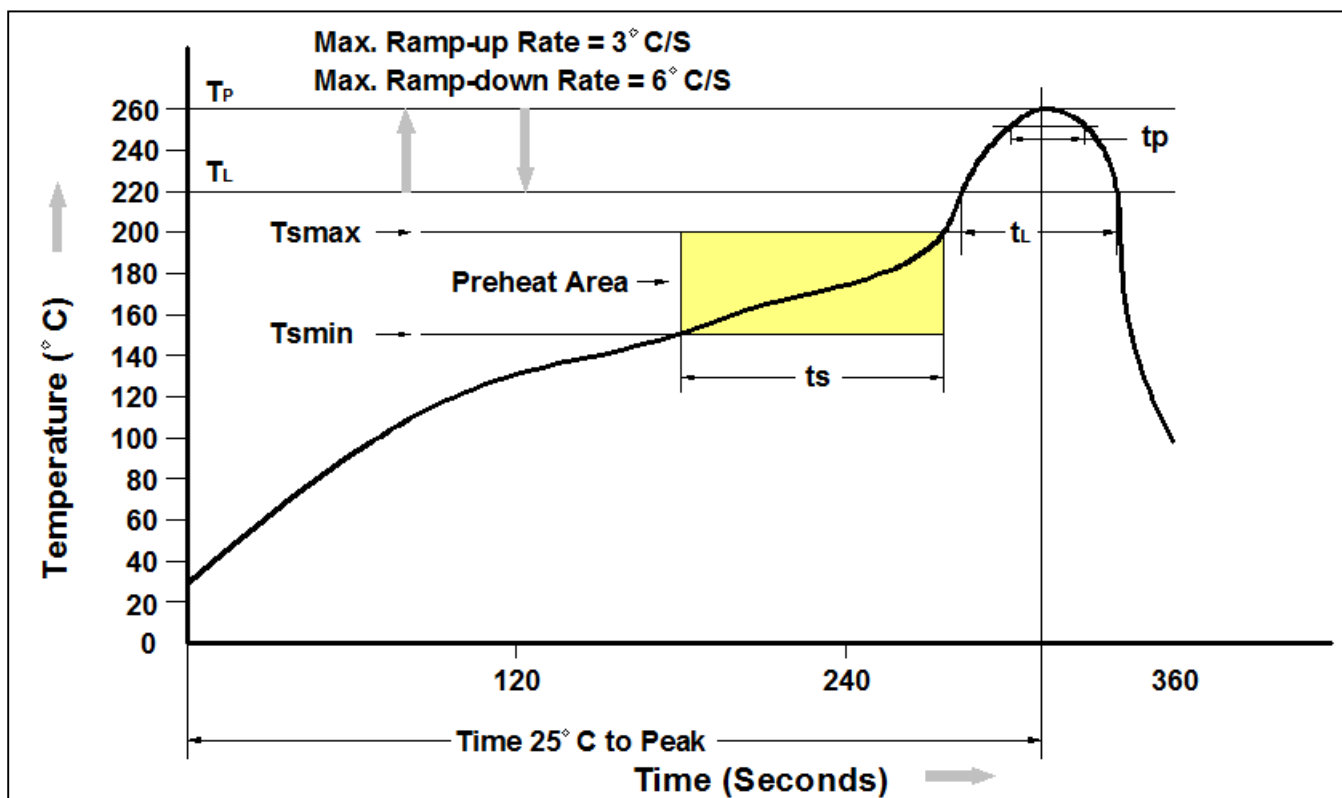
#### Option S(T2) & SL(T2)





## 2.5A MOSFET/IGBT Gate Driver Optocoupler

### Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150 °C
Temperature Max. (Tsmax)	200 °C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3 °C/second max.
Liquidous Temperature (T <sub>L</sub> )	217 °C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260 °C +0 °C / -5 °C
Time (t <sub>P</sub> ) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6 °C/second max
Time 25 °C to Peak Temperature	8 minutes max.



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